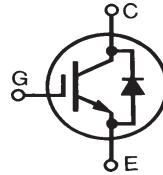


# HiPerFAST™ IGBT

IXGH 30N60B2D1  
IXGT 30N60B2D1

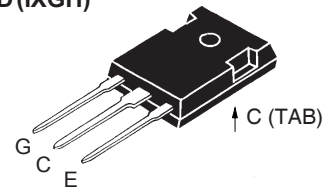
$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 70 \text{ A} \\ V_{CE(sat)} &< 1.8 \text{ V} \\ t_{fi typ} &= 82 \text{ ns} \end{aligned}$$

Optimized for 10-25 KHz hard switching and up to 150 KHz resonant switching

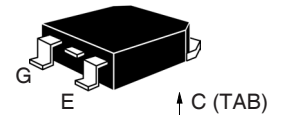


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1 \text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$ (limited by leads)	70	A
$I_{C110}$	$T_C = 110^\circ\text{C}$	30	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	150	A
<b>SSOA</b> <b>(RBSOA)</b>	$V_{GE} = 15 \text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 10 \Omega$ Clamped inductive load @ $\leq 600 \text{ V}$	$I_{CM} = 60$	A
$P_C$	$T_C = 25^\circ\text{C}$	190	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
$M_d$	Mounting torque (M3) (TO-247)	1.13/10Nm/lb.in.	
<b>Weight</b>	TO-247	6	g
	TO-268	4	g

TO-247 AD (IXGH)



TO-268 (IXGT)



G = Gate, C = Collector,  
E = Emitter, TAB = Collector

## Features

- Medium frequency IGBT
- Square RBSOA
- High current handling capability
- MOS Gate turn-on  
- drive simplicity

## Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

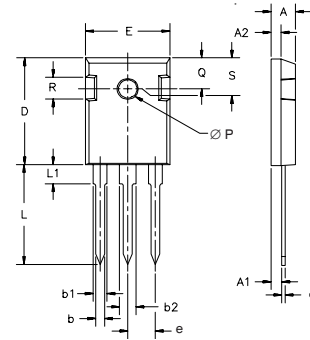
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$ , $V_{CE} = V_{GE}$	2.5		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$			$T_J = 25^\circ\text{C}$ : 200 $\mu\text{A}$ $T_J = 150^\circ\text{C}$ : 3 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}$ , $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = 24 \text{ A}$ , $V_{GE} = 15 \text{ V}$			$T_J = 25^\circ\text{C}$ : 1.8 V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$I_C = 24\text{ A}$ ; $V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	18	26	S	
$C_{ies}$ $C_{oes}$ $C_{res}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		1500	pF	
			145	pF	
			40	pF	
$Q_g$ $Q_{ge}$ $Q_{gc}$	$I_C = 24\text{ A}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 300\text{ V}$		66	nC	
			9	nC	
			22	nC	
$t_{d(on)}$ $t_{ri}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = 24\text{ A}$ , $V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}$ , $R_G = 5\ \Omega$		13	ns	
			15	ns	
			110	200	ns
			82	150	ns
			0.32	0.6	mJ
$t_{d(on)}$ $t_{ri}$ $E_{on}$ $t_{d(off)}$ $t_{fi}$ $E_{off}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = 24\text{ A}$ , $V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}$ , $R_G = 5\ \Omega$		13	ns	
			17	ns	
			0.22	mJ	
			200	ns	
			150	ns	
			0.9	mJ	
$R_{thJC}$ $R_{thCK}$	(TO-247)			0.65 K/W	
		0.25		K/W	

### Reverse Diode (FRED)

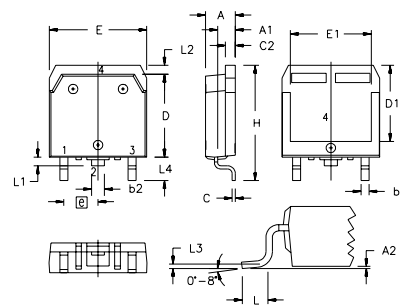
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_F$	$I_F = 30\text{ A}$ , $V_{GE} = 0\text{ V}$ , Pulse test $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$	$T_J = 150^\circ\text{C}$		1.6 2.5 V V
$I_{RM}$ $t_{rr}$	$I_F = 30\text{ A}$ , $V_{GE} = 0\text{ V}$ , $-di_F/dt = 100\text{ A}/\mu\text{s}$ , $T_J = 100^\circ\text{C}$ $V_R = 100\text{ V}$ , $T_J = 100^\circ\text{C}$ $I_F = 1\text{ A}$ ; $-di/dt = 100\text{ A}/\mu\text{s}$ ; $V_R = 30\text{ V}$		100	4 ns ns A
			25	ns
$R_{thJC}$				0.9 K/W

### TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

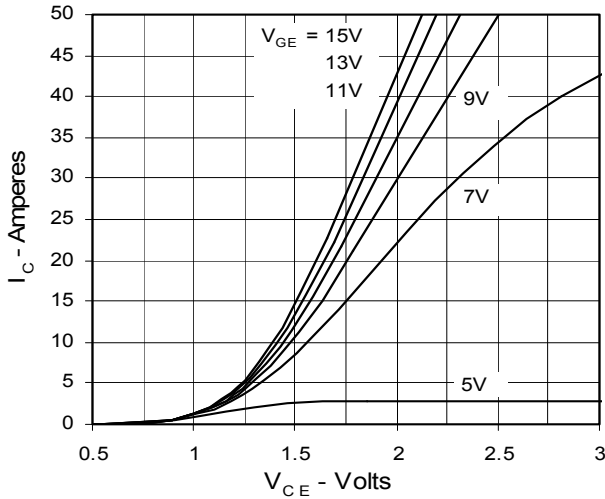
### TO-268 Outline



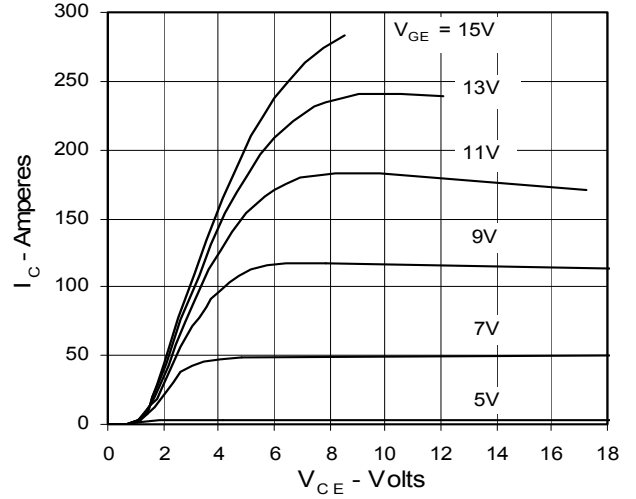
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

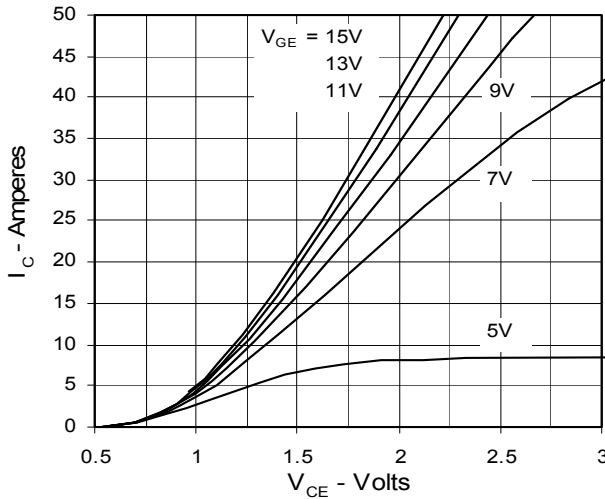
**Fig. 1. Output Characteristics @ 25 Deg. C**



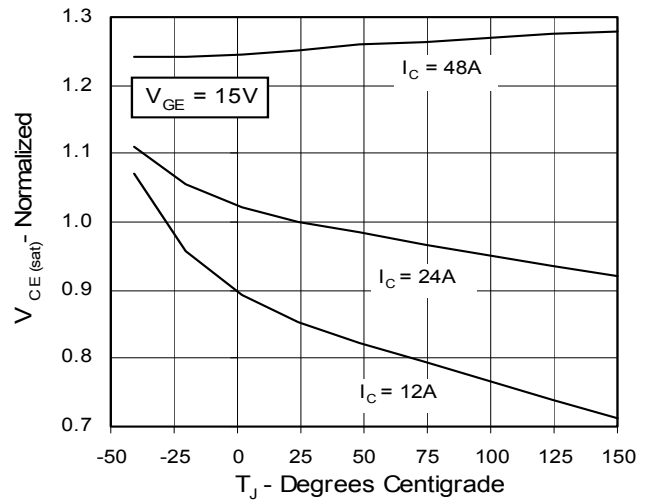
**Fig. 2. Extended Output Characteristics @ 25 deg. C**



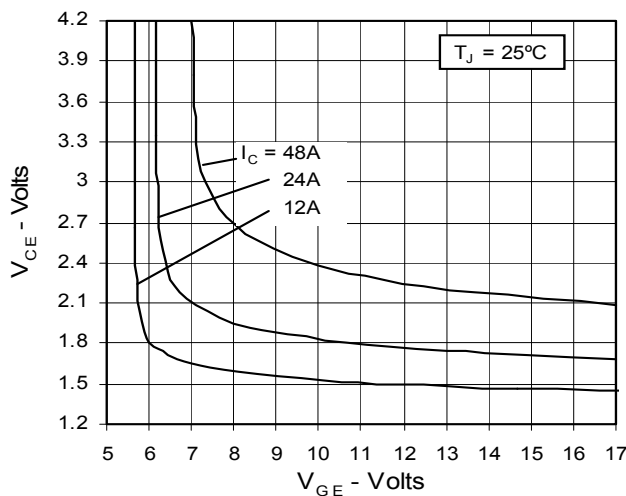
**Fig. 3. Output Characteristics @ 125 Deg. C**



**Fig. 4. Dependence of  $V_{CE(sat)}$  on Temperature**



**Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter voltage**



**Fig. 6. Input Admittance**

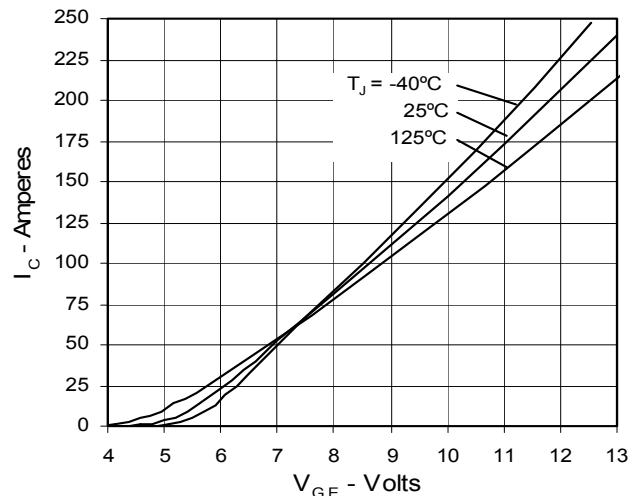


Fig. 7. Transconductance

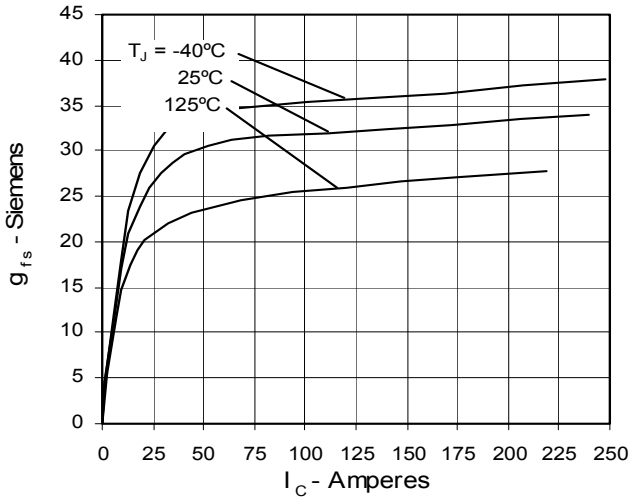


Fig. 8. Dependence of Turn-Off Energy on  $R_G$

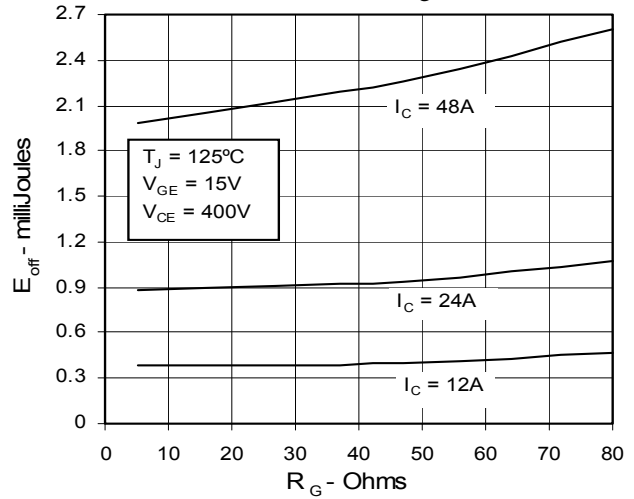


Fig. 9. Dependence of Turn-Off Energy on  $I_C$

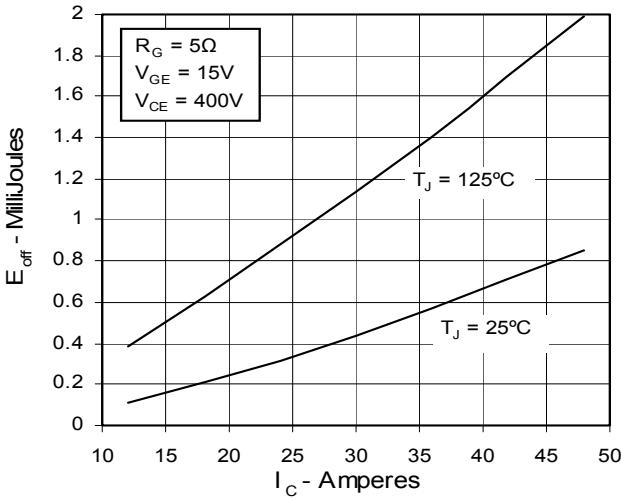


Fig. 10. Dependence of Turn-Off Energy on Temperature

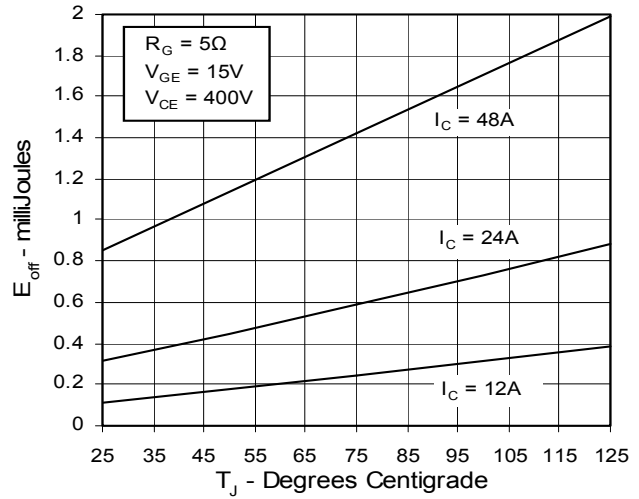


Fig. 11. Dependence of Turn-Off Switching Time on  $R_G$

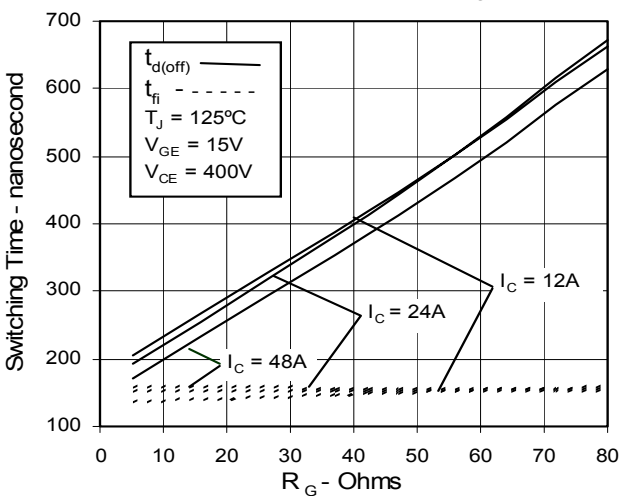
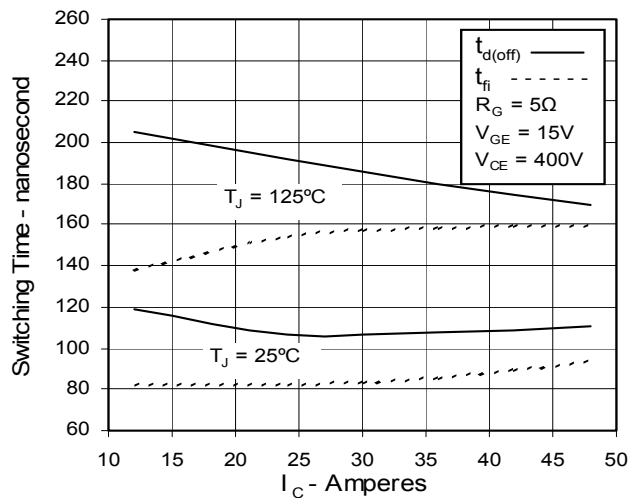
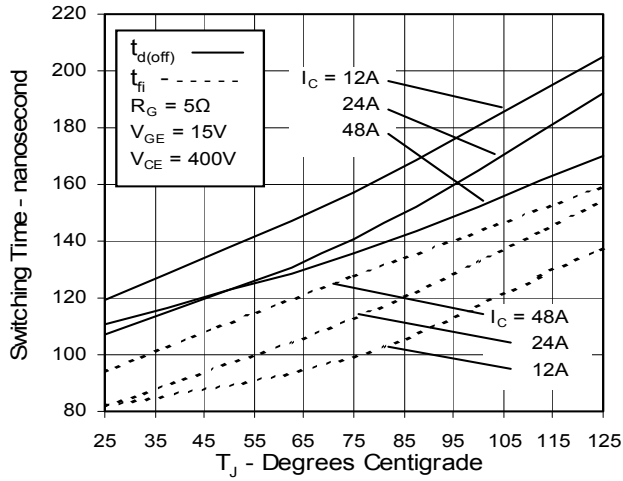


Fig. 12. Dependence of Turn-Off Switching Time on  $I_C$

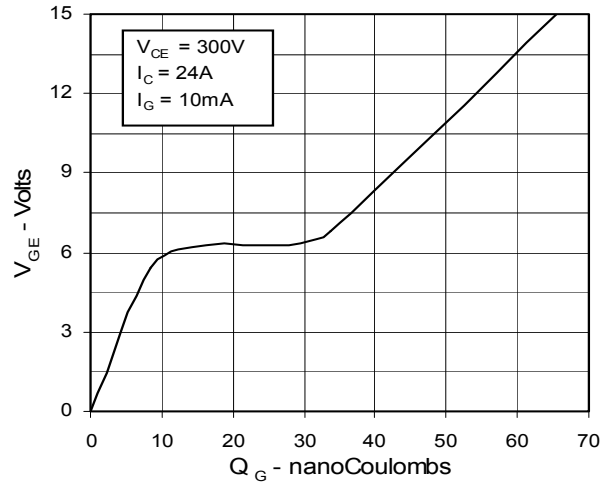


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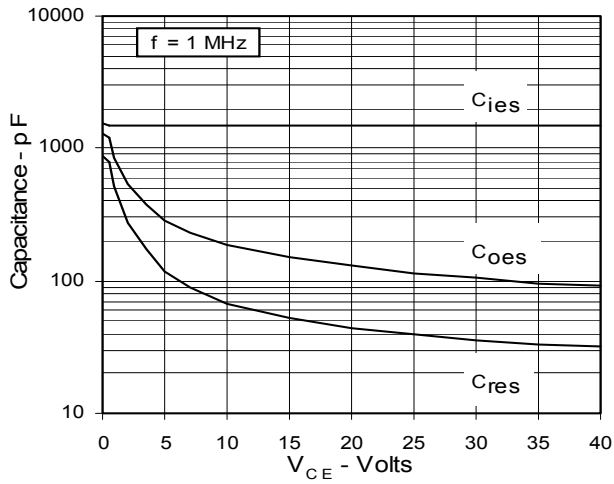
**Fig. 13. Dependence of Turn-Off Switching Time on Temperature**



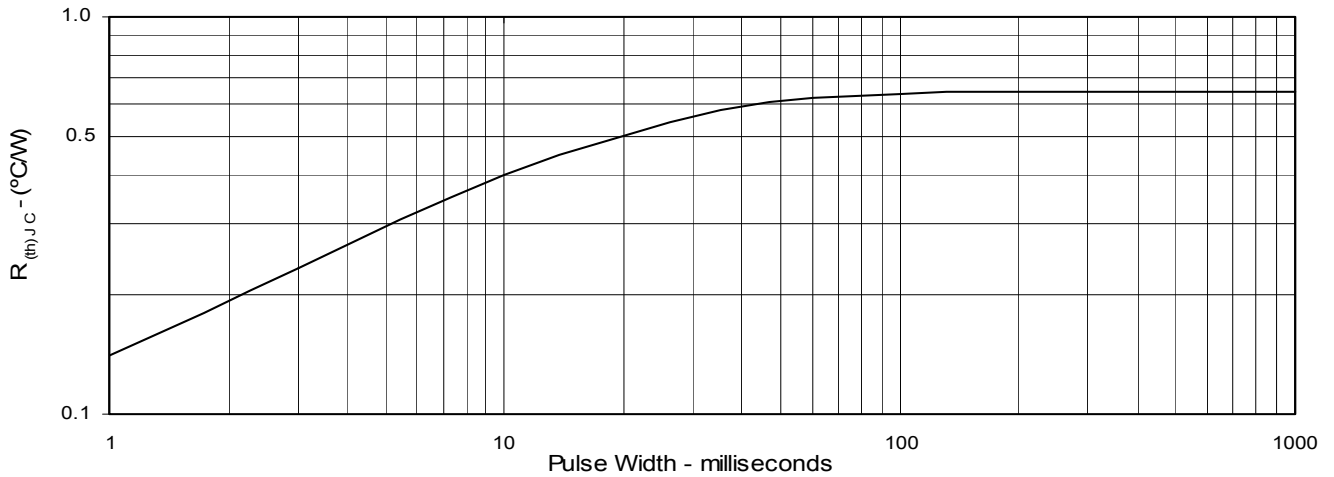
**Fig. 14. Gate Charge**



**Fig. 15. Capacitance**



**Fig. 16. Maximum Transient Thermal Resistance**



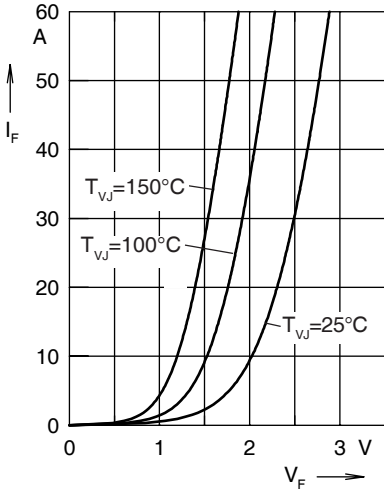


Fig. 17. Forward current  $I_F$  versus  $V_F$

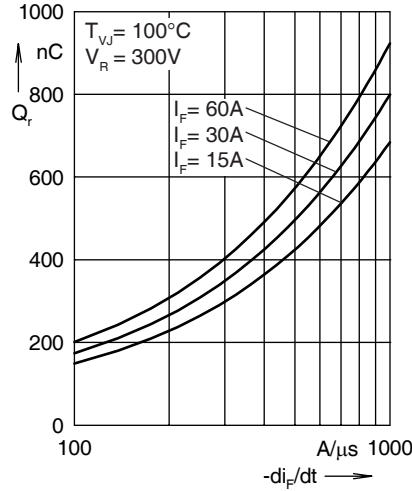


Fig. 18. Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

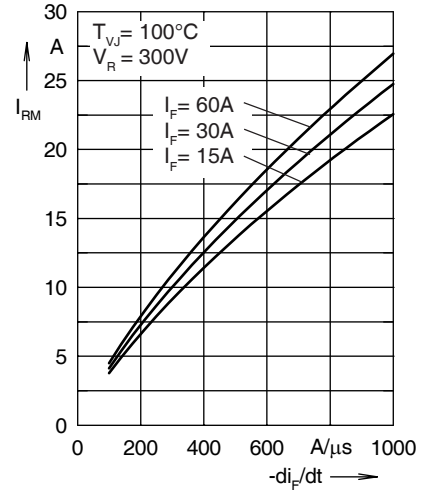


Fig. 19. Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

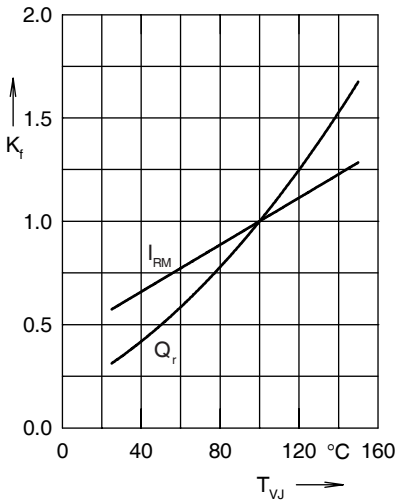


Fig. 20. Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

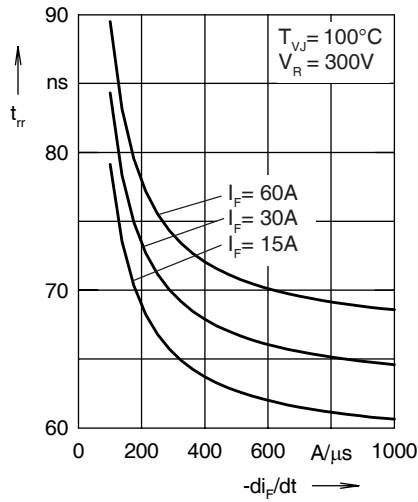


Fig. 21. Recovery time  $t_{rr}$  versus  $-di_F/dt$

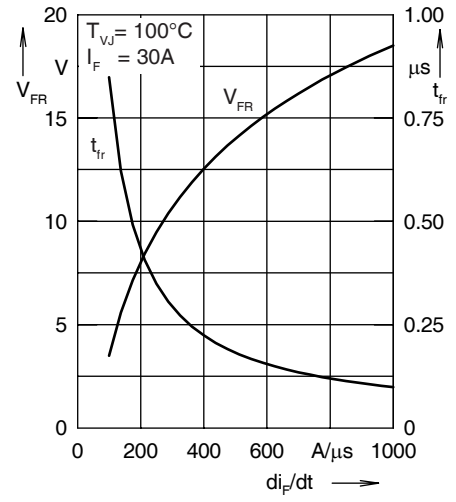


Fig. 22. Peak forward voltage  $V_{FR}$  and  $t_{fr}$  versus  $di_F/dt$

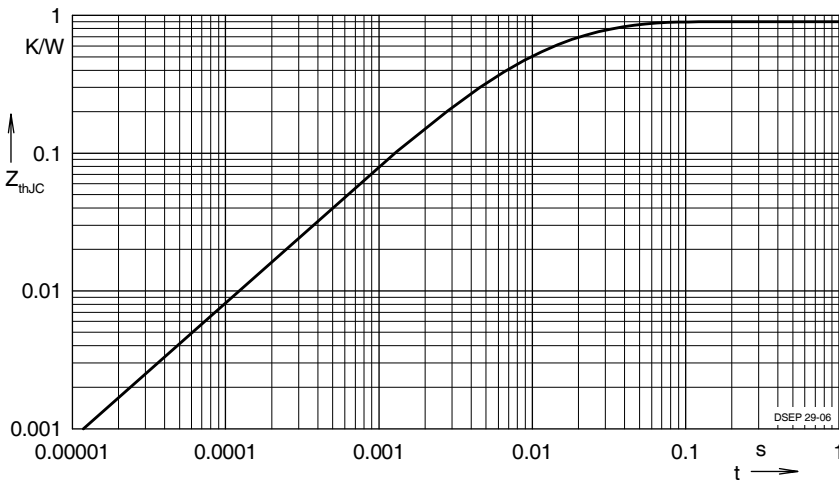


Fig. 23. Transient thermal resistance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343 6,583,505